

SILICON TRANSISTOR 2SB768

PNP SILICON TRIPLE DIFFUSED TRANSISTOR MP-3

DESCRIPTION

2SB768 is designed for Color TV Vertical Deflection Output, especially in Hybrid Integrated Circuits.

FEATURES

• High Voltage : VcEo = −150 V

• Complement to 2SD1033

QUALITY GRADE

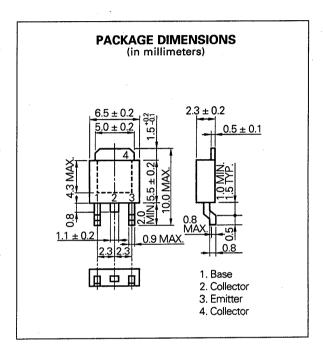
Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Collector to Base Voltage	Vсво	-200	٧
Collector to Emitter Voltage	Vceo	-150	٧
Emitter to Base Voltage	Vево	– 5	٧
Collector Current (DC)	İc	-2	Α
Collector Current (Pulse)*	lc	-3	Α
Total Power Dissipation (Ta = 25 °C)**	Рт	2.0	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

- * PW ≦ 10 ms, Duty Cycle ≦ 50 %
- ** When mounted on ceramic substrate of 7.5 $cm^2 \times 0.7$ mm



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

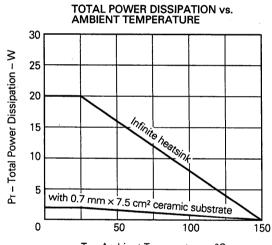
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			-50	μΑ	Vcs = -150 V, IE = 0
Emitter Cutoff Current	Ієво			-50	μА	VEB = -4.0 V, Ic = 0
DC Current Gain	hfe1***	40	80	200		Vce = -10 V, lc = -0.4 A
Collector Saturation Voltage	VCE(sat)***		-0.15	-1.0	V	lc = -500 mA, l _B = -50 mA
Gain Badnwidth Product	fī		10		MHz	VcE = -10 V, IE = -0.4 mA

^{***} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

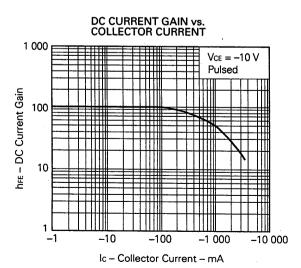
hre Classification

MARKING	M	L	К
hFE1	40 to 80	60 to 120	100 to 200

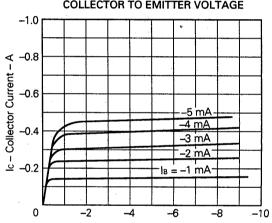
TYPICAL CHARACTERISTICS (Ta = 25 °C)



T₃ – Ambient Temperature – °C

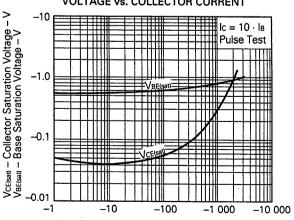


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



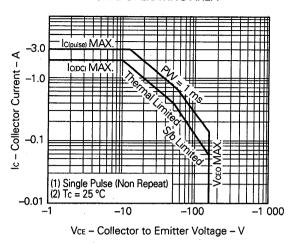
Vce - Collector to Emitter Voltage - V

BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT

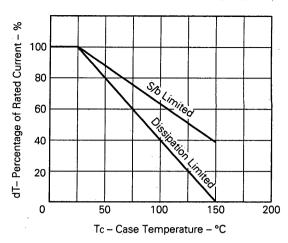


Ic - Collector Current - A

SAFE OPERATING AREA



DERATING OF SAFE OPERATING AREA



Reference

Application note name	No.
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207
Design of Push-Pull Type Switching Regulators (Basic).	TEB-1002
Design of Push-Pull Type Switching Regulators (Applications).	TEB-1003
Optimum Base Drive Conditions of Switching Power Transistors.	TEB-1014

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Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.

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